

Application No.: 10/784,773
Amendment Under 37 C.F.R. §1.111 dated November 22, 2004
Reply to the Office Action dated August 23, 2004

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claims 1-14 (canceled)

Claim 15 (Original): A method for fabricating a capacitor comprising the steps of:

- forming a lower electrode on a substrate;
- forming a capacitor dielectric film on the lower electrode;
- forming an upper electrode on the capacitor dielectric film;
- forming an insulation film on the upper electrode;
- forming an opening in the insulation film down to the lower electrode;
- forming a metal layer on the insulation film; and
- substituting a constituent atom of the lower electrode with a metal atom of the metal layer through the opening to thereby form the lower electrode of a metal substituted layer.

Claim 16 (Original): A method for fabricating a capacitor comprising the steps of:

- forming a lower electrode on a substrate;
- forming a capacitor dielectric film on the lower electrode;
- forming an upper electrode on the capacitor dielectric film;

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forming an insulation film on the upper electrode;

forming in the insulation film a first opening down to the lower electrode and a second opening down to the upper electrode;

forming a metal layer on the insulation film; and

substituting a constituent atom of the lower electrode with a metal atom of the metal layer through the first opening to thereby form the lower electrode of a metal substituted layer and substituting a constituent atom of the upper electrode with a metal atom of the metal layer through the second opening to thereby form the upper electrode of a metal substituted layer.

Claim 17 (Original): A method for fabricating a capacitor comprising the steps of:

forming a lower electrode on a substrate;

forming a capacitor dielectric film on the lower electrode;

forming an upper electrode on the capacitor dielectric film;

forming an insulation film on the upper electrode;

forming an opening in the insulation film down to the upper electrode;

forming a metal layer on the insulation film; and

substituting a constituent atom of the upper electrode with a metal atom of the metal layer through the opening to form the upper electrode of a metal substituted layer.

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Claim 18 (Original): A method for fabricating a capacitor according to claim 15, wherein a plurality of the sectional electrodes are formed in the step of forming the lower electrode and/or the step of forming the upper electrode.

Claim 19 (Original): A method for fabricating a capacitor according to claim 16, wherein a plurality of the sectional electrodes are formed in the step of forming the lower electrode and/or the step of forming the upper electrode.

Claim 20 (Original): A method for fabricating a capacitor according to claim 17, wherein a plurality of the sectional electrodes are formed in the step of forming the lower electrode and/or the step of forming the upper electrode.

Claim 21 (Original): A method for fabricating a capacitor according to claim 18, wherein in the step of forming the lower electrode and/or the step of forming the upper electrode, the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both ends of the sectional electrodes; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted with the metal from both ends of the sectional electrodes.

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Claim 22 (Original): A method for fabricating a capacitor according to claim 19, wherein
in the step of forming the lower electrode and/or the step of forming the upper electrode,
the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both
ends of the sectional electrodes; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of
forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted
with the metal from both ends of the sectional electrodes.

Claim 23 (Original): A method for fabricating a capacitor according to claim 20, wherein

in the step of forming the lower electrode and/or the step of forming the upper electrode,
the sectional electrodes are formed in a strip-shape;

in the step of forming the opening, a plurality of the openings are formed down to both
ends of the sectional electrodes; and

in the step of forming the lower electrode of the metal substituted layer and/or the step of
forming the upper electrode of the metal substituted layer, the sectional electrodes are substituted
with the metal from both ends of the sectional electrodes.

Claim 24 (Canceled)